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(74) Agent: AN, Sang, Jeong; 512-1906, 221, Gumi-dong, Bundang-gu, Seongnam-si, Kyunggi-do 463-715 (KR).

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(71) Applicant (for all designated States except US): SEOUL NATIONAL UNIVERSITY INDUSTRY FOUNDATION [KR/KR]; San 4-2 Bongcheon-dong, Kwanak-gu, Seoul 151-818 (KR).

(72) Inventors; and

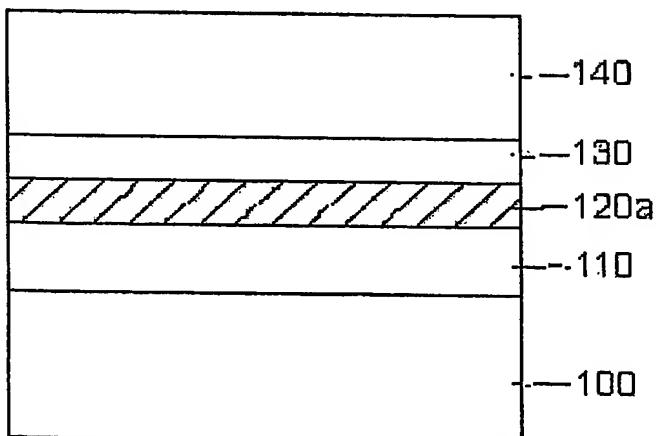
(75) Inventors/Applicants (for US only): YOON, Euijoon [KR/KR]; Rm.33-219, School of Materials Science and Engineering, Seoul National University, Seoul 151-742 (KR). NA, Hyunseok [KR/KR]; Rm.131-107, Research Institute of Advanced Materials, Seoul National University, Seoul 151-742 (KR).

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(54) Title: GROWTH METHOD OF NITRIDE SEMICONDUCTOR EPITAXIAL LAYERS



(57) Abstract: The present invention relates to a method for growing a nitride semiconductor epitaxial layer, which comprises the steps of growing a second nitride semiconductor epitaxial layer on a first nitride semiconductor epitaxial layer at a first temperature, growing a third nitride semiconductor epitaxial layer on the second nitride semiconductor epitaxial layer at a second temperature, and releasing nitrogen from the second nitride semiconductor epitaxial layer by increasing a temperature to a third temperature higher than the second temperature, thereby, it is possible to lower the defect density of epitaxial layers and reduce warpage of a substrate.